



501.38435VX1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: MITANI et al.  
Serial No.: 10/084,477  
Filed: February 28, 2002  
For: A SEMICONDUCTOR DEVICE  
Group: 2818  
Examiner: D. Nhu

-10-03

AMENDMENT

Assistant Commissioner  
for Patents  
Washington, D.C. 20231

February 24, 2003

Sir:

In response to the Office Action dated January 24, 2003, please amend the above-identified application as follows:

In the Claims:

Please add new claims 31 and 32 as follows:

-- 31. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer, a body electrode electrically connected to a channel forming region of said field effect transistor, and a back gate electrode provided below the insulating layer in an opposing relationship to the channel region of said field effect transistor, comprising steps of:

applying a first potential to the body electrode; and

applying a second potential to the back gate electrode

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